

Silicon PNP Power Transistor

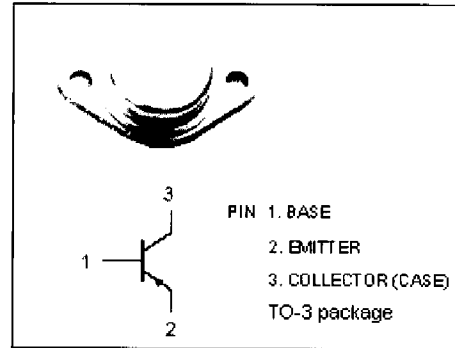
2SA753

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
 : $V_{(BR)CEO} = -110V(\text{Min.})$
- Complement to Type 2SC1343

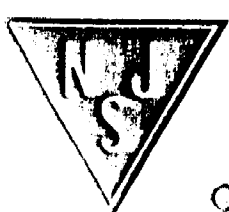
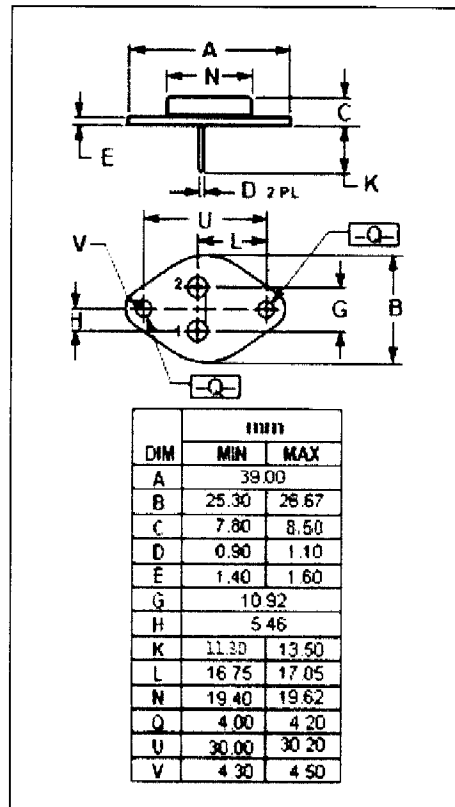
APPLICATIONS

- Designed for 100W audio amplifier power output applications.



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-140	V
V_{CEO}	Collector-Emitter Voltage	-110	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_C	Collector Current-Peak	-12	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	100	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; R _{BE} = ∞	-110			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -5mA; I _E = 0	-140			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -1A			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -140V; I _E = 0			-1	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -5V	30		200	
h _{FE-2}	DC Current Gain	I _C = -10A; V _{CE} = -5V	15			
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		20		MHz

◆ h_{FE-1} Classifications

A	B	C
30-60	50-120	100-200